

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Fast switching and soft recovery

## Applications

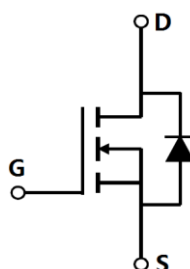
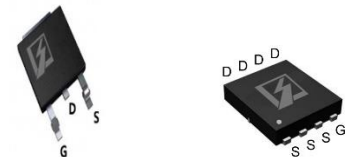
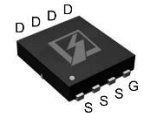
- ◆ Consumer electronic power supply
- ◆ Motor control
- ◆ Synchronous-rectification
- ◆ Isolated DC/DC convertor
- ◆ Invertors

## ■ General Description

SFG08R06xF use advanced SFGMOS™ technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable to use in Synchronous-rectification applications.

◆ $V_{DS, min}$	80 V
◆ $I_D, pulse$	300 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	6.5 mΩ
◆ $Q_g$	55.2 nC

## ■ Schematic and Package Information

<b>Schematic Diagram</b> 	<b>Pin Assignment Top View</b>  <b>TO252</b> <b>SFG08R06DF</b>	 <b>PDFN5x6</b> <b>SFG08R06GF</b>
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## ■ Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	80	V
Gate source voltage	$V_{GS}$	±20	V
Continuous drain current <sup>1)</sup>	$I_D$	100	A
Pulsed drain current <sup>2)</sup>	$I_{D, pulse}$	300	A
Power dissipation <sup>3)</sup>	$P_D$	148	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	80	mJ
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	°C

## ■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.84	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

## ■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	80			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	1.0		2.5	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		5.5	6.5	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=12\text{ A}$
Drain-source on-state resistance	$R_{DS(on)}$		7.5	9.0	$\text{m}\Omega$	$V_{GS}=4.5\text{ V}, I_D=10\text{ A}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		3869.9		pF	$V_{GS}=0\text{ V},$ $V_{DS}=40\text{ V},$ $f=100\text{ kHz}$
Output capacitance	$C_{oss}$		1304.2		pF	
Reverse transfer capacitance	$C_{rss}$		50.9		pF	
Turn-on delay time	$t_{d(on)}$		22.0		ns	$V_{GS}=10\text{ V},$ $V_{DS}=50\text{ V},$ $R_G=2\ \Omega,$ $I_D=25\text{ A}$
Rise time	$t_r$		21.5		ns	
Turn-off delay time	$t_{d(off)}$		62.7		ns	
Fall time	$t_f$		61.4		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		55.2		nC	$I_D=25\text{ A}$ , $V_{DS}=50\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		7.1		nC	
Gate-drain charge	$Q_{gd}$		14.6		nC	
Gate plateau voltage	$V_{\text{plateau}}$		3.4		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	$I_S$			100	A	$V_{GS} < V_{th}$
Pulsed source current	$I_{SP}$			300		
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=12\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		75.0		ns	$I_S=25\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		159.8		nC	
Peak reverse recovery current	$I_{rrm}$		3.4		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $R_G=25\text{ }\Omega$ ,  $L=0.3\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

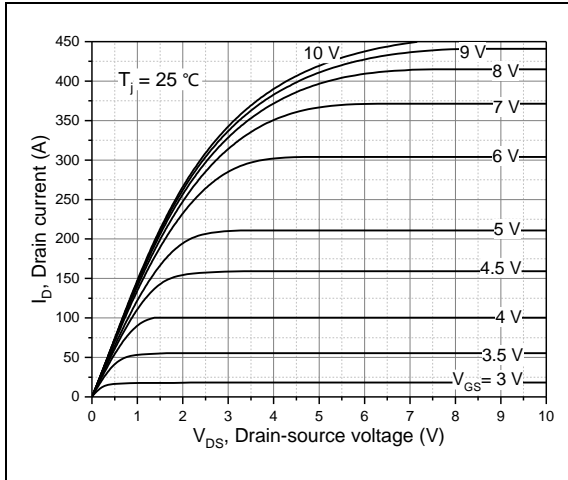


Figure 1, Typ. output characteristics

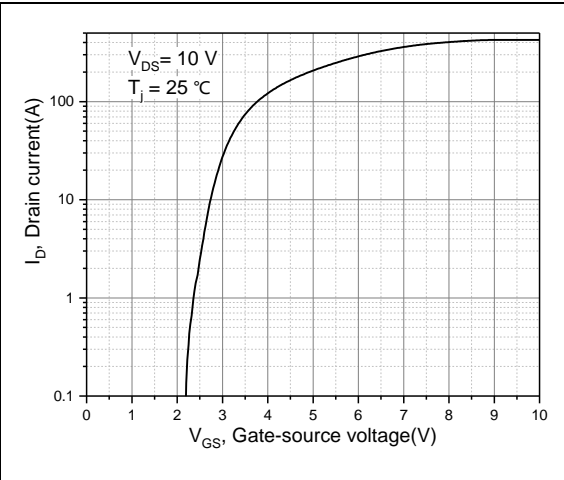


Figure 2, Typ. transfer characteristics

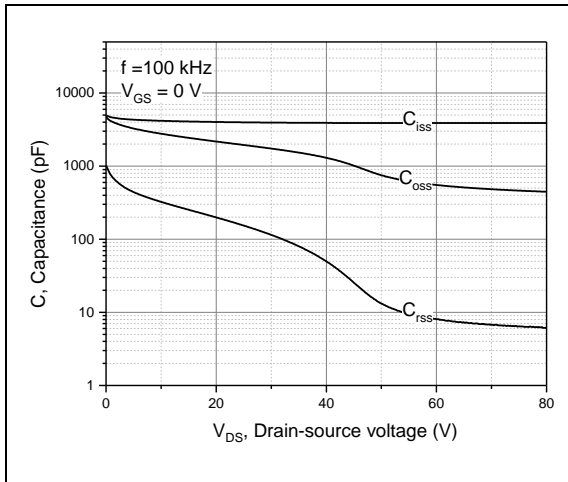


Figure 3, Typ. capacitances

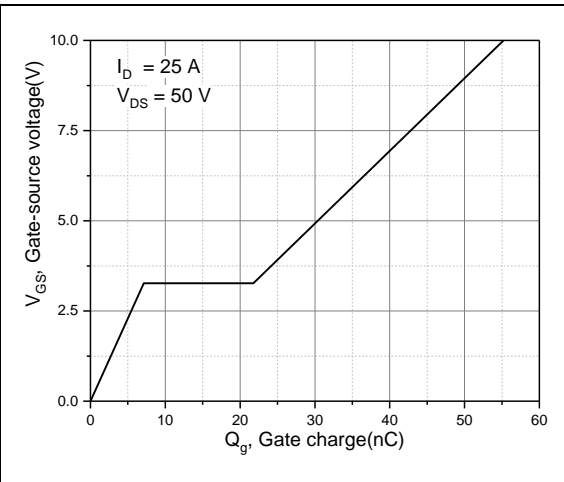


Figure 4, Typ. gate charge

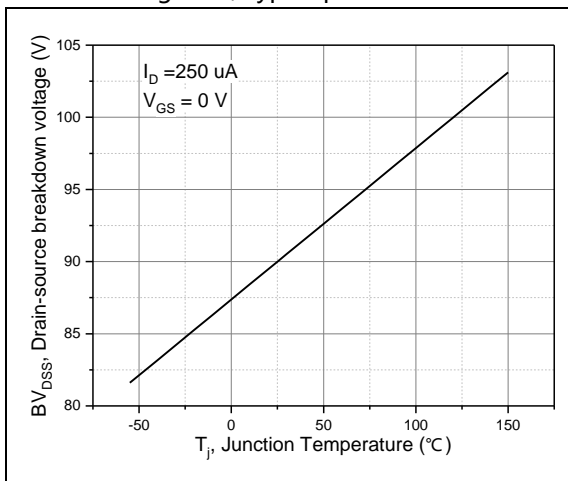


Figure 5, Drain-source breakdown voltage

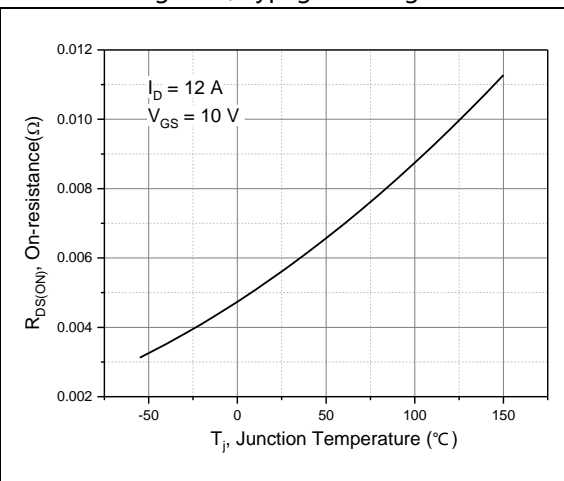


Figure 6, Drain-source on-state resistance

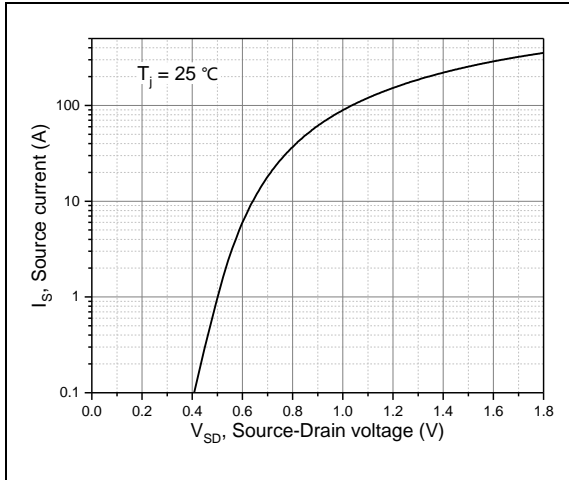


Figure 7, Forward characteristic of body diode

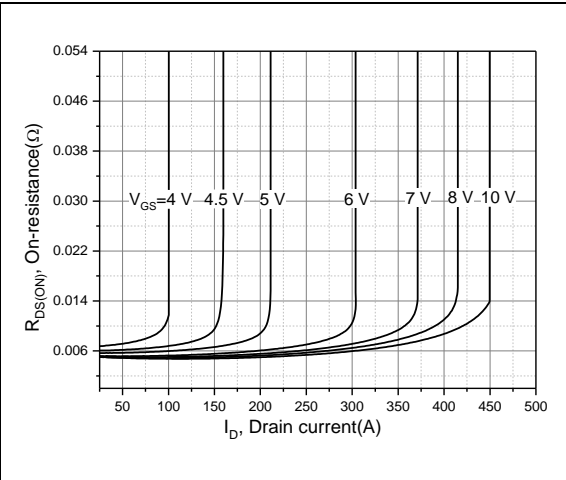


Figure 8, Drain-source on-state resistance

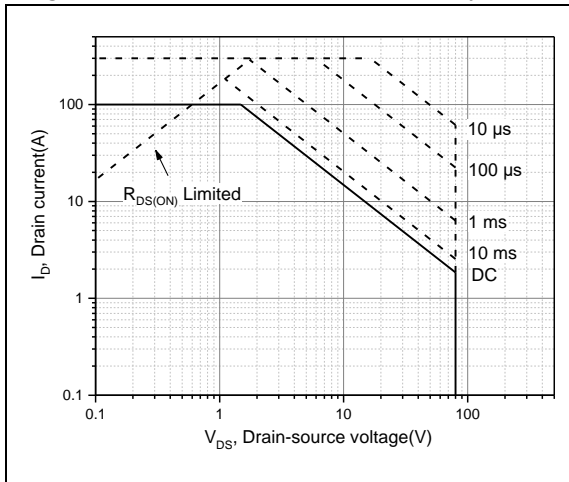
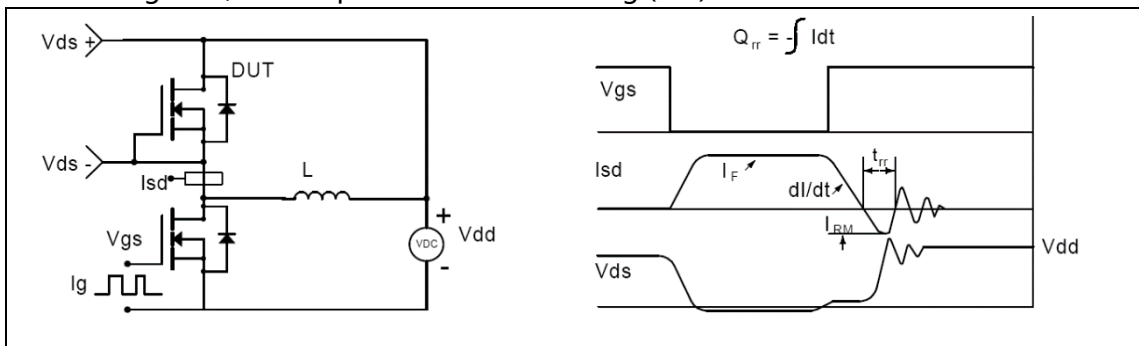
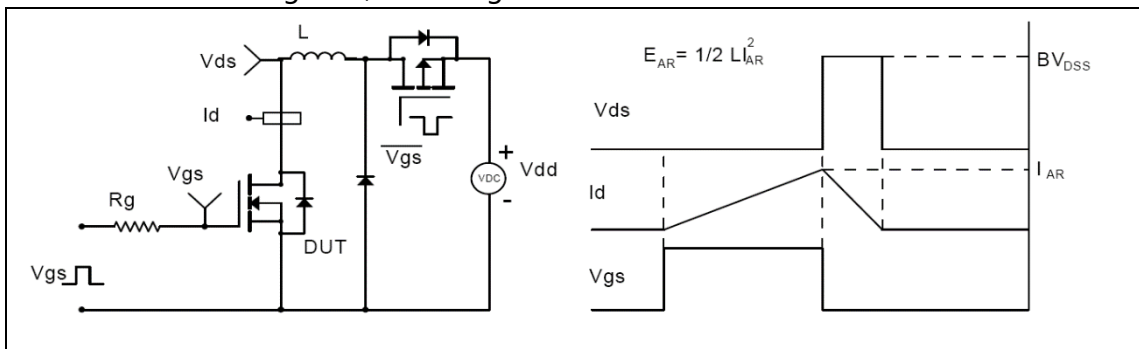
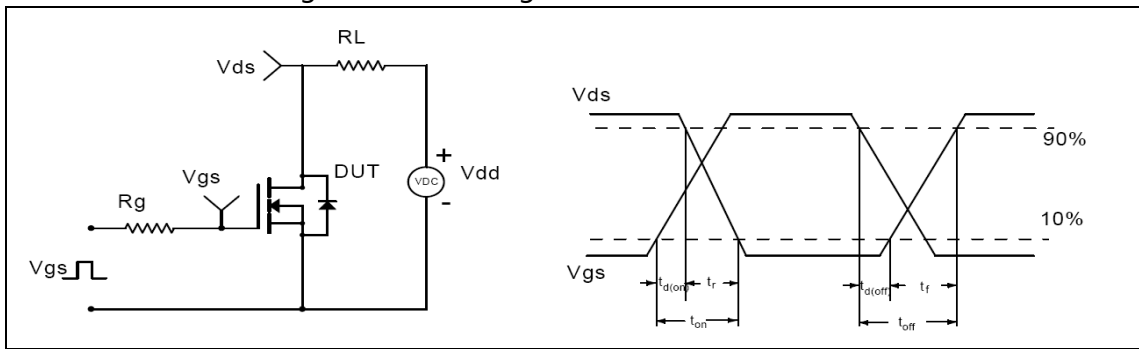
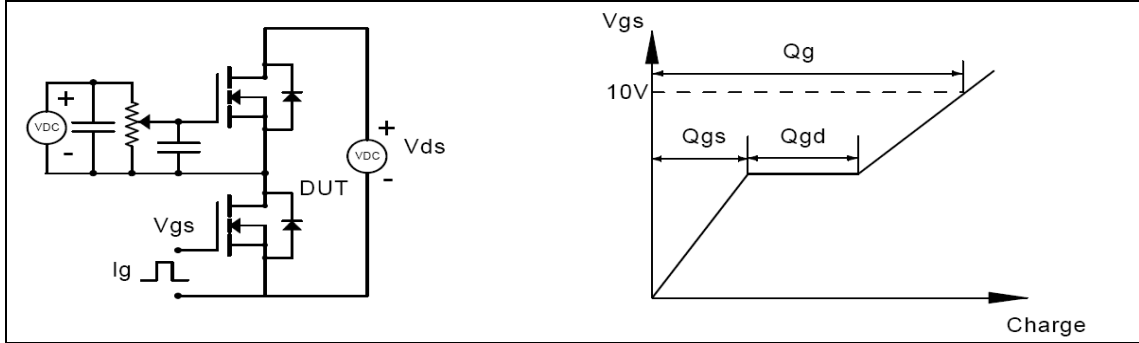


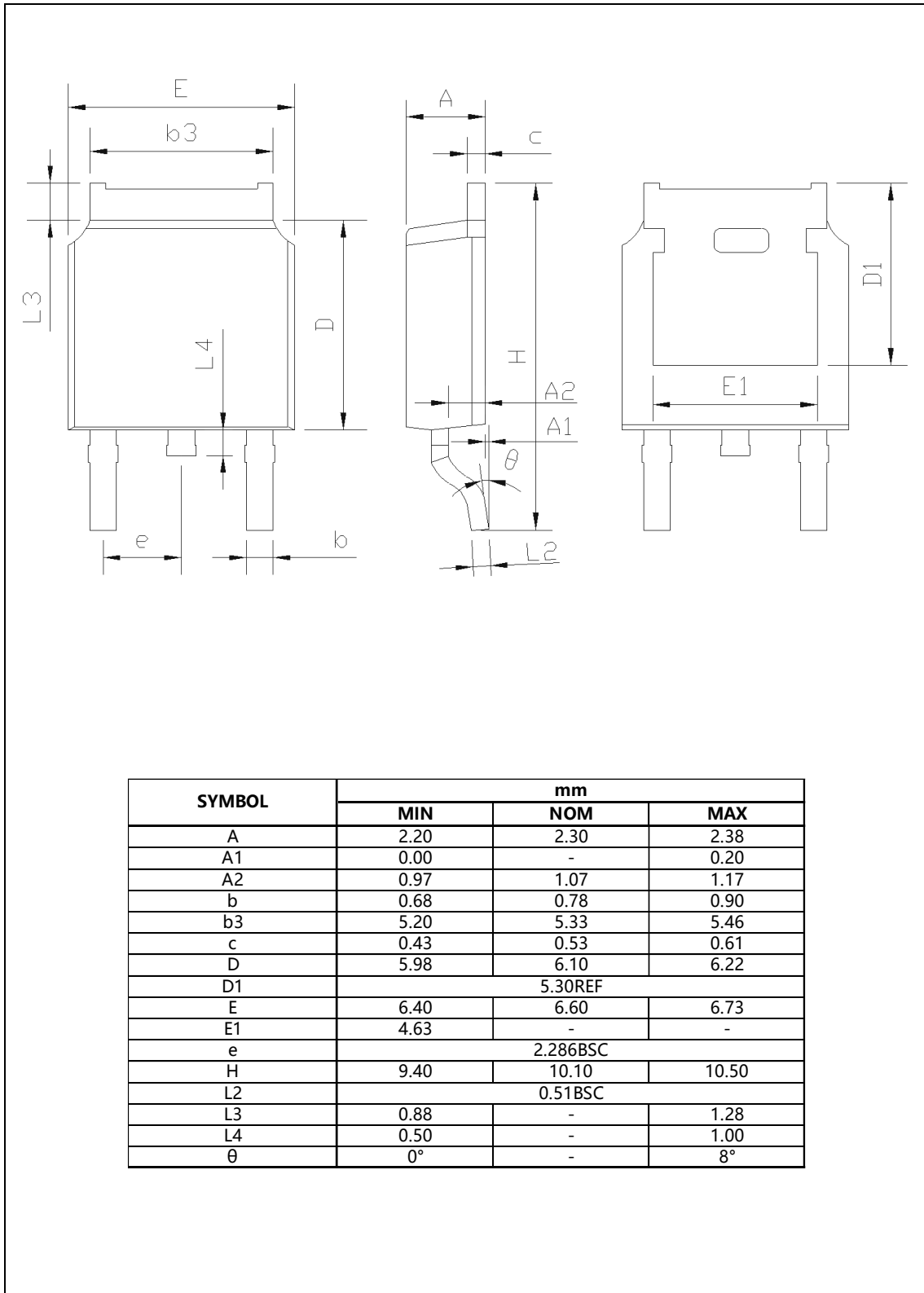
Figure 9, Safe operation area  $T_C=25\text{ }^{\circ}\text{C}$

■ Test circuits and waveforms



**■ Package Information**

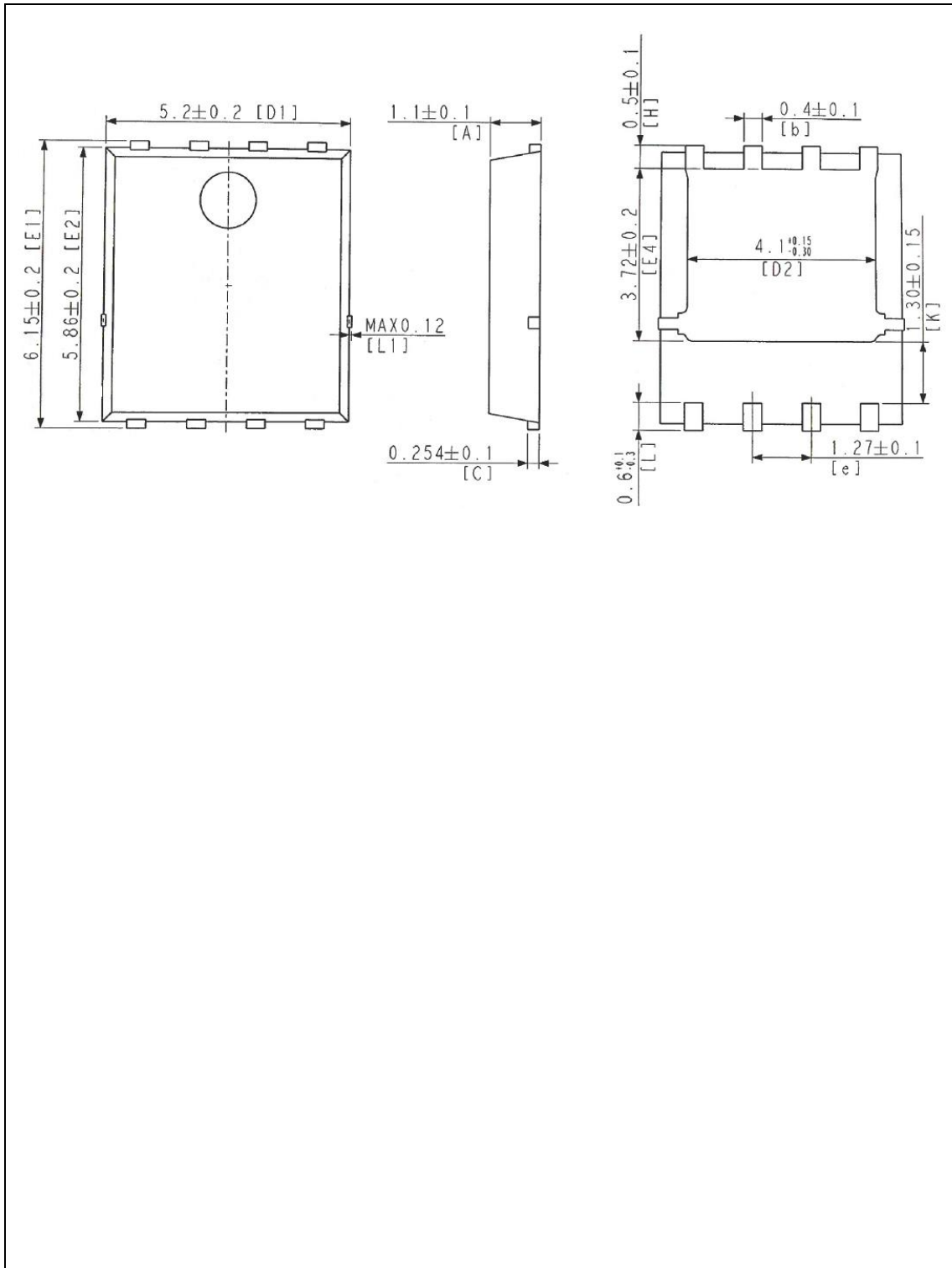
Figure1, TO252 package outline dimension





■ Package Information

Figure2, PDFN5×6 package outline dimension



## ■ Ordering Information

Package	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO252	2500	2	5000	5	25000
PDFN5×6	5000	2	10000	5	50000

## ■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG08R06DF	DPAK	yes	yes	yes
SFG08R06GF	PDFN5×6	yes	yes	yes